NSN 5962-01-287-3367

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View Online at https://aerobasegroup.com/nsn/5962-01-287-3367

Body Length:

Between 0.540 inches and 0.560 inches

Body Width:

Between 0.442 inches and 0.458 inches

Body Height:

Between 0.060 inches and 0.120 inches

Maximum Power Dissipation Rating:

1.0 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Electrostatic sensitive and low power and high speed

Inclosure Material:

Ceramic

Inclosure Configuration:

Leadless flat pack

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Input Circuit Pattern:

23 input

Case Outline Source And Designator:

C-12 mil-m-38510

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source

Time Rating Per Chacteristic:

30.00 nanoseconds propagation delay time, low to high level output and 30.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Ram

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

32 leadless

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

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